

FX607

N-Channel Silicon MOSFET

Ultrahigh-Speed Switching, Motor Driver Applications

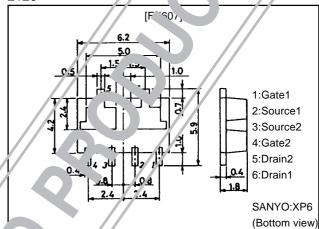
Features

- · Composite type composed of two low ON-resistance N-channel MOSFET chips for ultrahigh-speed switching and low-voltage drive.
- · Facilitates high-density mounting.
- The FX607 is formed with two chips, each being equivalent to the 2SK2260, placed in one package.
- · Matched pair characteristics.

Package Dimensions

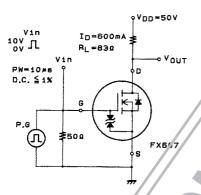
unit:mm

2120

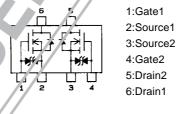


(Top view)

Switching Time Test CIrcuit



_`⊃c.rical Connection



Specifications

Absolute Maximum Ratings = 25°

Farameter	Sym'50l	Conditions	Ratings	Unit
Drain-to-Source \/ol'.age	Voss		150	V
Gate-to-Sourc/s Voltage	VGSS		±20	V
Drain Curre it (DC)	ID		1.2	Α
Drain Currer t (Pulse)	IDP	PW≤10µs, duty cycle≤1%	4.8	Α
Allowa'sle Power F supe n	PD	Tc=25°C, 1 unit	6	W
	PD	Mounted on ceramic board (750mm ² ×0.8mm) 1 unit	1.5	W
Total Dissipation	PT	Mounted on ceramic board (750mm ² ×0.8mm)	2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

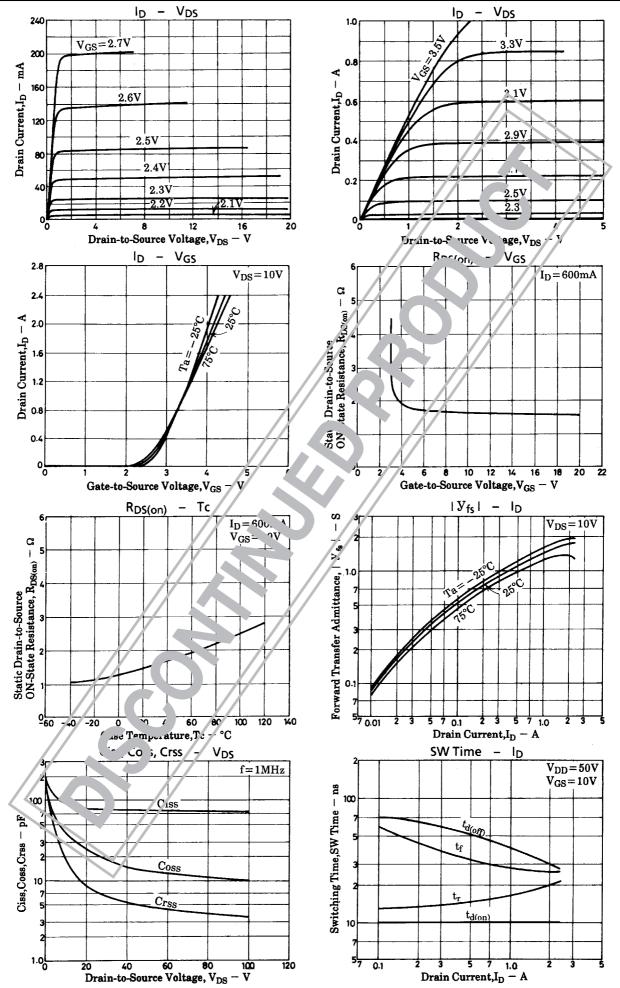
· Marking:607

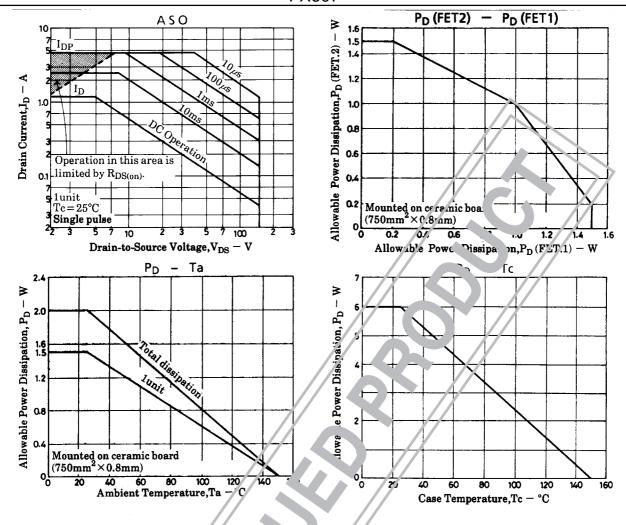
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Electrical Characteristics at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
D-S Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0	150			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =150V, V _{GS} =0			100	μA
Gate-to-Source Leakage Current	IGSS	V _{GS} =±18V, V _{DS} =0	//		±10	μA
Cutoff Voltage	VGS(off)	V _{DS} =10V, ID=1mA	1.5		2.5	V
Forward Transfer Admittance	Yfs	V _{DS} =10V, I _D =600mA	0	1.1		S
Static Drain-to-Source ON-State Resistance	R _{DS(on)}	I _D =600mA, V _{GS} =10V		1.6	2.2	Ω
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz				pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		25		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		8.5		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		10	7	ns
Rise Time	t _r	See specified Test Circuit		15		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit		50		ns
Fall Time	t _f	See specified Test Circuit		30		ns
Diode Forward Voltage	V _{SD}	I _S =1.2A, V _{GS} =0		1.0		V





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